



# **ELECTRONICS DEVICES AND CIRCUITS**

## **Section A**

### **Conducting Materials**

## OBJECTIVE

**DRIFT VELOCITY,  
COLLISION TIME,  
MEAN FREE PATH AND  
MOBILITY**

# DRIFT VELOCITY

- The drift velocity is the average velocity that a particle, such as an electron, attains due to an electric field. It can also be referred to as axial drift velocity since particles defined are assumed to be moving along a plane.
- In general, an electron will 'rattle around' in a conductor at the Fermi velocity randomly. An applied electric field will give this random motion a small net velocity in one direction.
- In a semiconductor, the two main carrier scattering mechanisms are ionized impurity scattering and lattice scattering.

# DRIFT VELOCITY

BECAUSE CURRENT IS PROPORTIONAL TO DRIFT VELOCITY, WHICH IS, IN TURN, PROPORTIONAL TO THE MAGNITUDE OF AN EXTERNAL ELECTRIC FIELD, OHM'S LAW CAN BE EXPLAINED IN TERMS OF **DRIFT VELOCITY.**

# Microscopic understanding of mobility?

❖ How long does a carrier move in time before collision ?

The average time taken between collisions is called as relaxation time,  $\tau$  (or mean free time)

❖ How far does a carrier move in space (distance) before a collision?

The average distance taken between collisions is called as mean free path,  $l$  .

# Calculation

Drift velocity = Acceleration x Mean free time

$$V_d = \frac{F}{m^*} \times \tau$$

Force is due to the applied field,  $F = qE$

$$V_d = \frac{F}{m^*} \times \tau = \frac{q E}{m^*} \tau$$

$$V_d = \mu E \Rightarrow \mu = \frac{q \tau}{m^*}$$

# Calculation

- Calculate the mean free time and mean free path for electrons in a piece of n-type silicon and for holes in a piece of p-type silicon.

$$\tau = ? \quad l = ? \quad m_e^* = 1.18 m_o \quad m_h^* = 0.59 m_o$$

$$\mu_e = 0.15 \text{ m}^2 / (\text{V} - \text{s}) \quad \mu_h = 0.0458 \text{ m}^2 / (\text{V} - \text{s})$$

$$\tau_e = \frac{\mu_e m_e^*}{q} = 10^{-12} \text{ sec} \quad \tau_h = \frac{\mu_h m_h^*}{q} = 1.54 \times 10^{-13} \text{ sec}$$

$$v_{th_{elec}} = 1.08 \times 10^5 \text{ m / s}$$

$$v_{th_{hole}} = 1.052 \times 10^5 \text{ m / s}$$

$$l_e = v_{th_{elec}} \tau_e = (1.08 \times 10^5 \text{ m / s})(10^{-12} \text{ s}) = 10^{-7} \text{ m}$$

$$l_h = v_{th_{hole}} \tau_h = (1.052 \times 10^5 \text{ m / s})(1.54 \times 10^{-13} \text{ sec}) = 2.34 \times 10^{-8} \text{ m}$$